UNISYS

DATE:

April 25, 1994

TO:

J. Denis/311.1

FROM:

K. Sahu/300.1 KS

SUBJECT:

Radiation Report on GOES/SXI

Part No. M38510/008-01BCA (5406)

Control No. 10702

cc:

L. Deemer/300.1

A. Sharma/311 Library/300.1

T. Sinacora/Aeroflex Laboratories, Inc.

PPM-94-011

A radiation evaluation was performed on 5406 (Hex Inverting Buffer) to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, four parts were irradiated under bias (see Figure 1 for bias configuration), and one part was used as a control sample. The total dose radiation levels were 10, 20, 30, 50, 75 and 100 krads*. The dose rate was between 0.37 and 1.25 krads/hour, depending on the total dose level (see Table II for radiation schedule). After the 100 krad irradiation, the parts were annealed for 168 hours at 25°C, after which the parts were annealed for 168 hours at 100°C. After each radiation exposure, parts were electrically tested according to the test conditions and the specification limits** listed in Table III. The electrical tests included three functional tests at 1.0 MHz, with $V_{\rm CC} = 4.50$ V, 5.00 V and 5.50 V.

All parts passed initial electrical measurements. All four irradiated parts passed all electrical measurements throughout all irradiation and annealing steps. No significant sensitivity to radiation was observed in any parameter. After annealing for 168 hours at 100°C, no rebound effects were observed.

Table IV provides the mean and standard deviation values for each parameter after different irradiation exposures and annealing steps.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

^{*}The term rads, as used in this document, means rads(silicon). All radiation levels cited are cumulative.

**These are manufacturer's non-irradiated data specification limits. No post-irradiation limits were provided by the manufacturer at the time these tests were performed.

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TABLE I. Part Information

Generic Part Number:

5406

GOES/SXI

Part Number:

M38510/00801BCA*

GOES/SXI

Control Number:

10701

Charge Number:

C42992

Manufacturer:

ΤI

Lot Date Code:

9333G

Quantity Tested:

5

Serial Number of

Control Sample:

51

Serial Numbers of

Radiation Samples:

52, 53, 54, 55

Part Function:

Hex Inverting Buffer

Part Technology:

Bipolar

Package Style:

14-pin DIP

Test Equipment:

s-50

Test Engineer:

T. Mondy

^{*} No radiation tolerance/hardness was guaranteed by the manufacturer for this part.

TABLE II. Radiation Schedule for 5406

EVENTS	DATE
1) INITIAL ELECTRICAL MEASUREMENTS	03/25/94
2) 10 KRAD IRRADIATION (0.50 KRADS/HOUR)	03/28/94
POST-10 KRAD ELECTRICAL MEASUREMENT	03/29/94
3) 20 KRAD IRRADIATION (0.50 KRADS/HOUR)	03/29/94
POST-20 KRAD ELECTRICAL MEASUREMENT	03/30/94
4) 30 KRAD IRRADIATION (0.50 KRADS/HOUR)	03/30/94
POST-30 KRAD ELECTRICAL MEASUREMENT	03/31/94
5) 50 KRAD IRRADIATION (1.00 KRADS/HOUR)	03/31/94
POST-50 KRAD ELECTRICAL MEASUREMENT	04/01/94
6) 75 KRAD IRRADIATION (0.37 KRADS/HOUR)	04/01/94
POST-75 KRAD ELECTRICAL MEASUREMENT	04/04/94
7) 100 KRAD IRRADIATION (1.25 KRADS/HOUR)	04/04/94
POST-100 KRAD ELECTRICAL MEASUREMENT	04/05/94
8) 168-HOUR ANNEALING @25°C	04/05/94
POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENTS	04/12/94
9) 168-HOUR ANNEALING @100°C*	04/12/94
POST-168 HOUR ANNEAL ELECTRICAL MEASUREMENTS	04/19/94

^{*}High temperature annealing is performed to accelerate long term time dependent effects (TDE), namely, the "rebound" effect, due to the growth of interface states after the radiation exposure. For more information on the need to perform this test, refer to MIL-STD-8830, Method 1019, Para. 3.10.1.

Table III. Electrical Characteristics of 5406

		FUN	ICTÍONAL TESTS	PERFORME	
PARAMETER HUNCT 1 FUNCT 2 FUNCT 3	VCC VIL 4.5V 0.0V 5.0V 0.0V 5.5V 0.0V LOAD US	5.5V	CONDITIONS ====================================	PINS ALL I/O ALL I/O ALL I/O	LIMITS AT +25C ONLY VOL<2.0V / VOH>2.0V: VOL<2.0V / VOH>2.0V: VOL<2.0V / VOH>2.0V
		DC P	ARAMETRIC TEST	S PERFOR	1ED
PARAMETER	VCC VIL	VIH	CONDITIONS	PINS	LIMITS @ +25C
VOL1	4.5V 0.0V	2.00	LUAD=30.GMA	DUTS	>+0.0V , <+0.7V
VOL2	4.5V 0.0V	5.5V 2.0V 5.5V	LUAD=16.0MA	STUO	>+0.0V , <+0.4V
ICEX	4.5V 0.8V	5.5V	VTST=+30.0V	DUTS	>+0.0A / <+250UA
VIC	4.5V 0.8V	5.5V	ITST=-12MA	INS	>-1.5V / <+0.0V
IIH1 IIH2	5.5V 0.0V 5.5V 0.0V	5.5V 5.5V	VIN = 2.4V VIN = 5.5V	INS INS	>+0.0UA / <+40.0UA >+0.0UA / <+100UA
IIL	5.5V 0.0V	5.50	VIN = 0.4V	INS	>-1.3MA / <-0.4MA
ICCH	5.5V 0.0V 5.5V 0.0V	5.5V 5.5V	VIN = 5.5V VIN = 0.0V	V C C	>+0.0UA / <+48.0MA >+0.0UA / <+51.0MA

Total Dose Exposures and Annealing for M38510/008-01BCA (5406) /1 TABLE IV: Summary of Electrical Measurements after

								lota	1 Do	Se	Total Dose Exposure	ure	(krads)	ds)			7	Anne	Annealing	
Spec.			Initial	ial	10	0	20	0	3	30	50	0	75	2	Ē	100	168	urs	168 hrs 168 hrs	ırs
Lim. /2	7																@25°C		@100°C	<u> </u>
min ma	Ë	max	mean	sd	теап	ജർ	mean	sd	mean	ಬ್ಡಿ	mean	sd	mean	sd 1	mean	sd	mean	sd	mean	sd
			PASS		PASS		PASS		PASS		PASS		PASS		PASS		PASS	000000	PASS	
			PASS		PASS		PASS		PASS		PASS		PASS		Pass		PASS	200000	PASS	Į.
	İ		PASS		PASS		PASS		SSVd	:	PASS		PASS		PASS		PASS	*****	PASS	
0 7	7	700	265	8.0	268	9.3	274	14	270	14	272	12	292	26	279	14	270	9.4	280	11
0	4	400	189	5.2	191	5.8	361	9.0	261	7.3	193	7.2	209	18	199	10	193	5.8	198	6.1
0	2	250	10.0	. 02	0	.02	0.0	.02	0	.01	¢.	.01	0.02	.02	0,02	.02	o	.01	0.02	.04
-1.5		0	00.7	.01	10 1	.01	00.1	.01	1:01	.01	1.01	.01	66.0	.01	1.00	.01	1.00	.01	66.0-	0.
0	4	40	£ .93	.31	4.87	.31	6.93	.31	4.64	.30	06'7	.30	4.99	.32	6 6	.30	9. 5.	.30	5,24	.31
0	-	100	s: 70	.37	5.57	.36	\$9.5	.36	88.8	.35	5.63	.36	5.72	.37	s: 75	.35	¥9.5	.35	66.5	.36
-1300 -	ì	-400	-716	2.5	-717	2.4	-715	2.7	-111	2.7	-716	2.7	-713	2.5	-713	2.6	ST C	2.6	-710	2.8
0		48	6.38	.12	35.9	90.	35.8	.10	35.8	.07	35.8	.07	15. 15.	.20	35.7	.07	38.7	.11	35.6	.12
0		51.	33.2	.07	33.2	90.	1 EE	.10	33.2	.07	33.1	.10	33.0	.10	33.0	.10	33.0	.07	32.8	10
	-	1																		

- The mean and standard deviation values were calculated over the four parts irradiated in this testing. The control sample remained constant throughout the testing and is not included in this table. 1/
 - These are manufacturers' non-irradiated data sheet specification limits. No post-irradiation limits were provided by the manufacturer at the time the tests were performed. 7/2
 - "PASS" means that all irradiated parts passed this functional test at this irradiation or annealing level. "FAIL" means that all irradiated parts failed this test at this irradiation or annealing level. "nPmF" means that n parts passed and m parts failed the test at this level. 3/

Figure 1. Radiation Bias Circuit for 5406



